PCFG40T120SQF

IGBT Die

Trench Ultra Field Stop IGBT Die optimized for UPS and Solar applications.

Features

- Extremely Efficient Trench with Field Stop Technology
- Low V_{CE(sat)} Loss Reduces System Power Dissipation
- Optimized for High Speed Switching

Typical Applications

- Solar Inverters
- UPS Systems

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector–Emitter Voltage, T _J = 25°C	V_{CE}	1200	V
DC Collector Current, limited by max T _{J(max)}	Ic	(Note 1)	Α
Pulsed Collector Current (Note 2)	I _{C, pulse}	160	Α
Gate-Emitter Voltage	V_{GE}	±20	V
Maximum Junction Temperature	T_J	-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Depending on thermal properties of assembly. 2. T_{pulse} limited by T_{jmax} , 10 μ Sec pulse V_{GE} = 15 V.

MECHANICAL DATA

Parameter	Value	Unit	
Die Size	5384 x 4184	μ m ²	
Emitter Pad Size	See die layout μm²		
Gate Pad Size	405 x 660	μm ²	
Die Thickness	112	μm	
Wafer Size	150	mm ²	
Top Pad Metal	5 μm AlCu		
Back Metal	2 μm AlTiNiAg		
Passivation	1.5 μm HR NIT		
Max possible chips per wafer	551		
Reject Ink dot size	25 mils		
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28°C, 30–65% RH	Type: Sawn wafer on tape. Storage time: <3 months		

ORDERING INFORMATION

Device	Inking?	Shipping
PCFG40T120SQF	Yes	Sawn Wafer on Tape

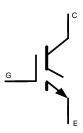


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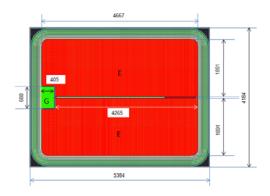
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 $V_{CE} = 1200 \text{ V}$ I_C = Limited by $T_{J(max)}$

IGBT DIE



DIE OUTLINE



1

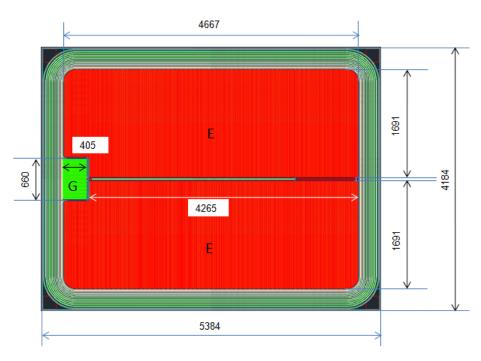
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ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$, unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Units
STATIC CHARACTERISTICS	•	1			•	•
Collector-Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V, } I_{C} = 500 \mu\text{A}$	V _{(BR)CES}	1200	-	-	V
Collector-Emitter Saturation Voltage	V _{GE} = 15 V, I _C = 40 A	V _{CE(sat)}	_	1.7	1.95	V
Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_{C} = 400 \mu A$	V _{GE(TH)}	4.5	5.5	6.5	V
Collector–Emitter Cutoff Current	V _{GE} = 0 V, V _{CE} = 1200 V	I _{CES}	_	-	400	μΑ
Gate Leakage Current	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0 \text{ V}$	I _{GES}	_	-	±200	nA
DYNAMIC CHARACTERISTICS	·					
Input Capacitance		C _{ies}	_	4912	-	pF
Output Capacitance	$V_{CE} = 20 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz	C _{oes}	_	140	-	
Reverse Transfer Capacitance	1 – 1 111112	C _{res}	_	80	-	
Gate Charge Total		Qg	_	212	-	nC
Gate-Emitter Charge	$V_{CE} = 600 \text{ V}, V_{GE} = 15 \text{ V},$ $I_{C} = 40 \text{ A}$	Q _{ge}	_	43	_	
Gate-Collector Charge		Q _{gc}	-	102	-	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DIE LAYOUT



E = Emitter Pad G = Gate Pad All dimensions in μm

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